

7MBR150XRA065-50

IGBT Modules

Power Module(X series)
650V / 150A / PIM

■ Features

- Low $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant Product

■ Applications

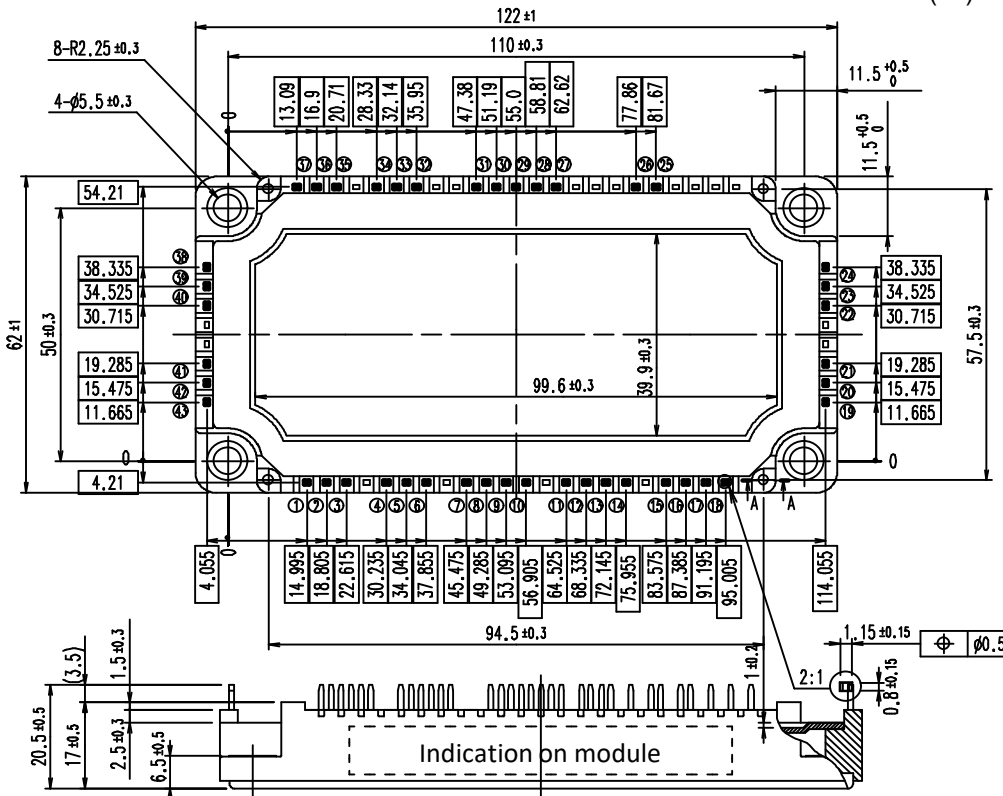
- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterrupted Power Supply

■ Typical appearance



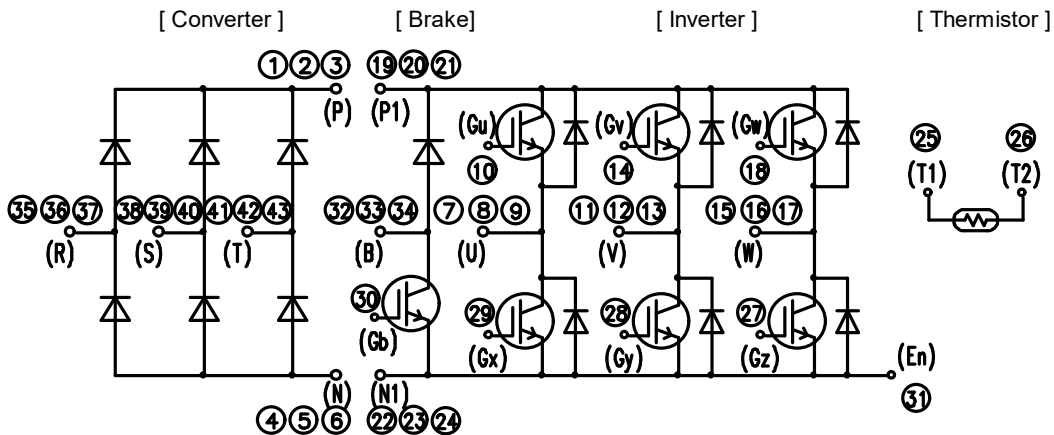
■ Outline drawing (Unit : mm)

shows theoretical dimension.
() shows reference dimension.



Section A-A
Weight: 310 g (typ.)

■ Equivalent circuit



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IGBT Modules
■ Maximum ratings (at $T_c = 25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units
Inverter	Collector-Emitter voltage	V_{CES}			650	V
	Gate-Emitter voltage	V_{GES}			± 20	V
	Collector current	I_C	Continuous	$T_c=80^\circ\text{C}$	150	A
		I_C pulse	1ms		300	
	Forward current	I_F	Continuous		150	
		I_F pulse	1ms		300	
Collector power dissipation	P_C	1 device		450	W	
Brake IGBT	Collector-Emitter voltage	V_{CES}			650	V
	Gate-Emitter voltage	V_{GES}			± 20	V
	Collector current	I_C	Continuous	$T_c=80^\circ\text{C}$	75	A
		I_C pulse	1ms		150	
Collector power dissipation	P_C	1 device		270	W	
Brake FWD	Forward current	I_F	Continuous		50	A
		I_{FRM}	1ms		100	
	Repetitive peak reverse voltage	V_{RRM}			650	V
Converter	Repetitive peak reverse voltage	V_{RRM}			800	V
	Average output current	I_O	Three-phase full wave rectified current	$T_c=80^\circ\text{C}$	150	A
	Surge current (Non-Repetitive) (*1)	I_{FSM}	$t=10\text{ms}$, Half sine wave form	$T_{vj}=25^\circ\text{C}$	1440	A
				$T_{vj}=150^\circ\text{C}$	1260	
	I^2t (Non-Repetitive) (*1)	I^2t		$T_{vj}=25^\circ\text{C}$	10400	A^2s
			$T_{vj}=150^\circ\text{C}$	8000		
Junction temperature	T_{vj}	Inverter, Brake		175	$^\circ\text{C}$	
		Converter		150		
Operating junction temperature (under switching conditions)	T_{vjop}	Inverter, Brake		175		
		Converter		150		
Case temperature	T_c			125		
Storage temperature	T_{stg}			-40 ~ 125		
Isolation voltage	between terminals and copper base (*2)	V_{isol}	A.C. : 1min.		2500	Vrms
	between thermistor and others (*3)					
Screw torque	Mounting torque of screws to heat sink	M_5	M5		2.5~6.0	N·m

(*1) T_{vj} : Temperature at test start.

(*2) All terminals should be connected together during the test.

(*3) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

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IGBT Modules
■ Electrical characteristics (at $T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero Gate voltage collector current	I_{CES}	$V_{GE} = 0\text{V}$ $V_{CE} = 650\text{V}$	-	-	50	μA	
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}$ $V_{GE} = +20/-20\text{V}$	-	-	100	nA	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}$ $I_C = 150\text{mA}$	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15\text{V}$ $I_C = 150\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	1.65	2.10	V
			$T_{vj}=25^{\circ}\text{C}$	-	1.30	1.75	
	$T_{vj}=125^{\circ}\text{C}$		-	1.45	-		
	$T_{vj}=150^{\circ}\text{C}$		-	1.50	-		
	$V_{CE(sat)}$ (chip)		$T_{vj}=175^{\circ}\text{C}$	-	1.55	-	
Internal Gate resistance	r_g	-	-	4.50	-	Ω	
Capacitance	C_{ies}	$V_{CE} = 10\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	17.2	-	nF	
	C_{oes}		-	0.66	-		
	C_{res}		-	0.23	-		
Gate charge	Q_G	$V_{CC} = 300\text{V}$ $V_{GE} = -15 \rightarrow +15\text{V}$ $I_C = 150\text{A}$	-	1200	-	nC	
Forward voltage	V_F (terminal)	$I_F = 150\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	1.90	2.35	V
	V_F (chip)		$T_{vj}=25^{\circ}\text{C}$	-	1.55	2.00	
			$T_{vj}=125^{\circ}\text{C}$	-	1.50	-	
			$T_{vj}=150^{\circ}\text{C}$	-	1.50	-	
			$T_{vj}=175^{\circ}\text{C}$	-	1.45	-	
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 300\text{V}$ $I_C, I_F = 150\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 18\ \Omega$	$T_{vj}=25^{\circ}\text{C}$	-	0.48	-	μs
			$T_{vj}=125^{\circ}\text{C}$	-	0.52	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.54	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.52	-	
	t_r		$T_{vj}=25^{\circ}\text{C}$	-	0.12	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.16	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.16	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.18	-	
	$t_{d(off)}$		$T_{vj}=25^{\circ}\text{C}$	-	0.54	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.58	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.59	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.60	-	
t_f	$T_{vj}=25^{\circ}\text{C}$	-	0.05	-			
	$T_{vj}=125^{\circ}\text{C}$	-	0.05	-			
	$T_{vj}=150^{\circ}\text{C}$	-	0.06	-			
	$T_{vj}=175^{\circ}\text{C}$	-	0.06	-			
Reverse recovery time	t_{rr}	$T_{vj}=25^{\circ}\text{C}$	-	0.11	-		
		$T_{vj}=125^{\circ}\text{C}$	-	0.23	-		
		$T_{vj}=150^{\circ}\text{C}$	-	0.24	-		
		$T_{vj}=175^{\circ}\text{C}$	-	0.30	-		

 (*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

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Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Inverter Switching loss (per pulse)	E_{on}	$V_{CC} = 300V$ $I_C, I_F = 150A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 18 \Omega$	$T_{Vj} = 25^\circ C$	-	5.94	-	mJ
			$T_{Vj} = 125^\circ C$	-	8.59	-	
			$T_{Vj} = 150^\circ C$	-	9.46	-	
			$T_{Vj} = 175^\circ C$	-	10.27	-	
	E_{off}	$V_{CC} = 300V$ $I_C, I_F = 150A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 18 \Omega$	$T_{Vj} = 25^\circ C$	-	4.86	-	
			$T_{Vj} = 125^\circ C$	-	6.19	-	
			$T_{Vj} = 150^\circ C$	-	6.48	-	
			$T_{Vj} = 175^\circ C$	-	6.81	-	
	E_{rr}	$V_{CC} = 300V$ $I_C, I_F = 150A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 18 \Omega$	$T_{Vj} = 25^\circ C$	-	0.64	-	
			$T_{Vj} = 125^\circ C$	-	0.90	-	
			$T_{Vj} = 150^\circ C$	-	1.12	-	
			$T_{Vj} = 175^\circ C$	-	1.24	-	
Zero Gate voltage collector current	I_{CES}	$V_{GE} = 0V$ $V_{CE} = 650V$	-	-	50	μA	
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0V, \quad V_{GE} = +20/-20V$	-	-	100	nA	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_C = 75A$	$T_{Vj} = 25^\circ C$	-	1.45	1.95	V
			$T_{Vj} = 25^\circ C$	-	1.30	1.75	
	$T_{Vj} = 125^\circ C$		-	1.45	-		
	$T_{Vj} = 150^\circ C$		-	1.50	-		
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (chip)	$T_{Vj} = 150^\circ C$	-	1.50	-		
		$T_{Vj} = 175^\circ C$	-	1.55	-		
		$T_{Vj} = 175^\circ C$	-	1.55	-		
		$T_{Vj} = 175^\circ C$	-	1.55	-		
Internal Gate resistance	r_g	-	-	0	-	Ω	
Brake Switching time (*1)	$t_{d(on)}$	$V_{CC} = 300V$ $I_C = 75A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 43 \Omega$	$T_{Vj} = 25^\circ C$	-	0.35	-	μs
			$T_{Vj} = 125^\circ C$	-	0.34	-	
			$T_{Vj} = 150^\circ C$	-	0.36	-	
			$T_{Vj} = 175^\circ C$	-	0.34	-	
	t_r	$V_{CC} = 300V$ $I_C = 75A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 43 \Omega$	$T_{Vj} = 25^\circ C$	-	0.12	-	
			$T_{Vj} = 125^\circ C$	-	0.14	-	
			$T_{Vj} = 150^\circ C$	-	0.16	-	
			$T_{Vj} = 175^\circ C$	-	0.15	-	
	$t_{d(off)}$	$V_{CC} = 300V$ $I_C = 75A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 43 \Omega$	$T_{Vj} = 25^\circ C$	-	0.47	-	
			$T_{Vj} = 125^\circ C$	-	0.52	-	
			$T_{Vj} = 150^\circ C$	-	0.52	-	
			$T_{Vj} = 175^\circ C$	-	0.53	-	
	t_f	$V_{CC} = 300V$ $I_C = 75A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 43 \Omega$	$T_{Vj} = 25^\circ C$	-	0.04	-	
			$T_{Vj} = 125^\circ C$	-	0.05	-	
			$T_{Vj} = 150^\circ C$	-	0.04	-	
			$T_{Vj} = 175^\circ C$	-	0.04	-	
Reverse current	I_{RRM}	$V_R = 650V$	-	-	50	μA	
Forward voltage	V_F (terminal)	$I_F = 50A$	$T_{Vj} = 25^\circ C$	-	1.70	2.20	V
			$T_{Vj} = 25^\circ C$	-	1.55	2.00	
	$T_{Vj} = 125^\circ C$		-	1.50	-		
	$T_{Vj} = 150^\circ C$		-	1.50	-		
Forward voltage	V_F (chip)	$T_{Vj} = 175^\circ C$	-	1.45	-		
		$T_{Vj} = 175^\circ C$	-	1.45	-		
		$T_{Vj} = 175^\circ C$	-	1.45	-		
		$T_{Vj} = 175^\circ C$	-	1.45	-		
Reverse current	I_{RRM}	$V_R = 800V$	-	-	50	μA	
Forward voltage	V_{FM}	$I_F = 150A$	terminal	-	1.45	1.90	V
			chip	-	1.10	1.55	
Thermistor Resistance	R	$T = 25^\circ C$	-	5000	-	Ω	
		$T = 100^\circ C$	465	495	520		
B value	B	$T = 25/50^\circ C$	3305	3375	3450	K	

(*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

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NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

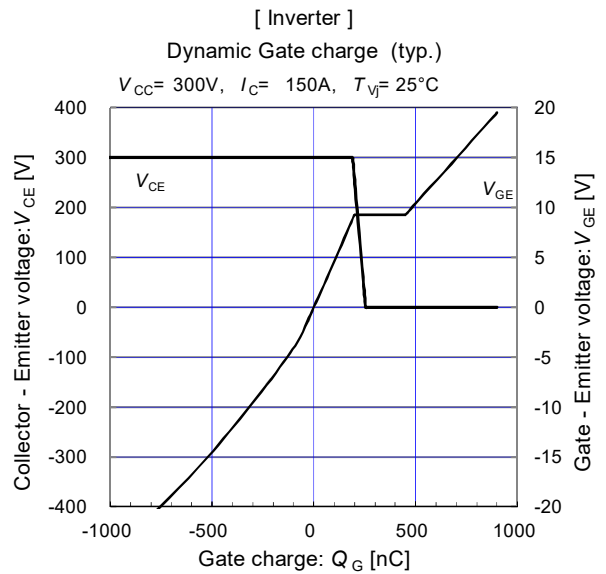
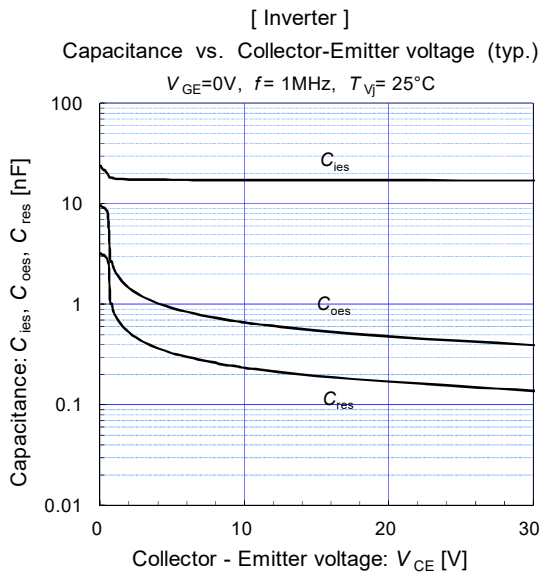
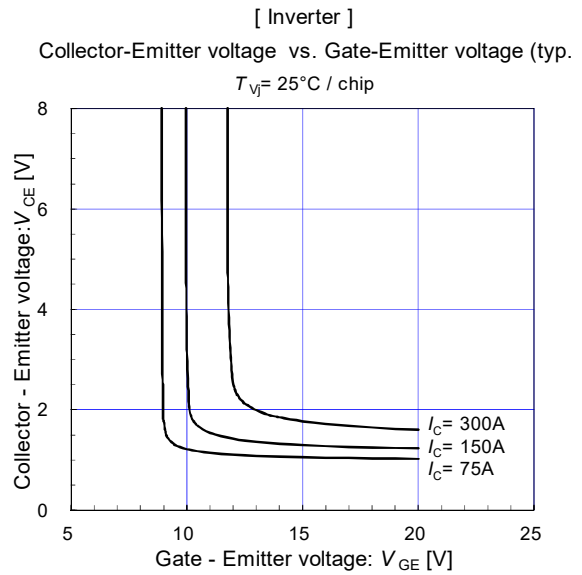
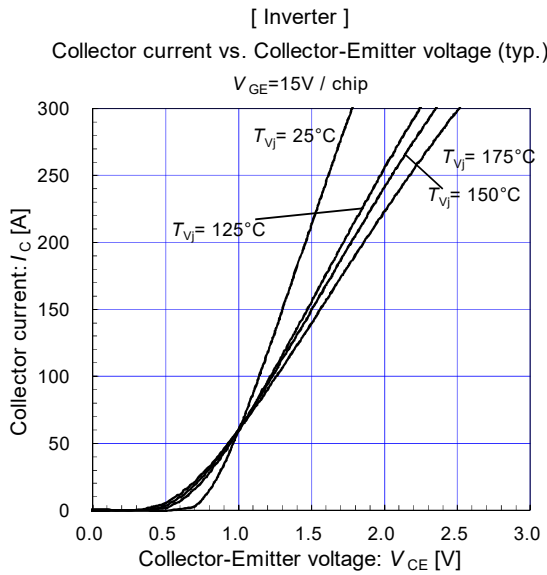
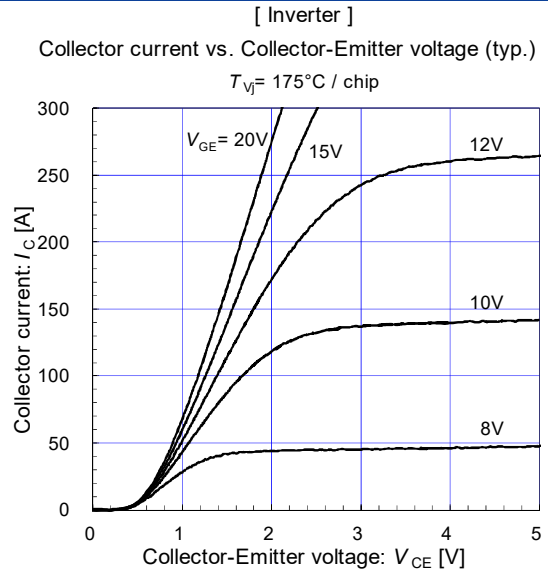
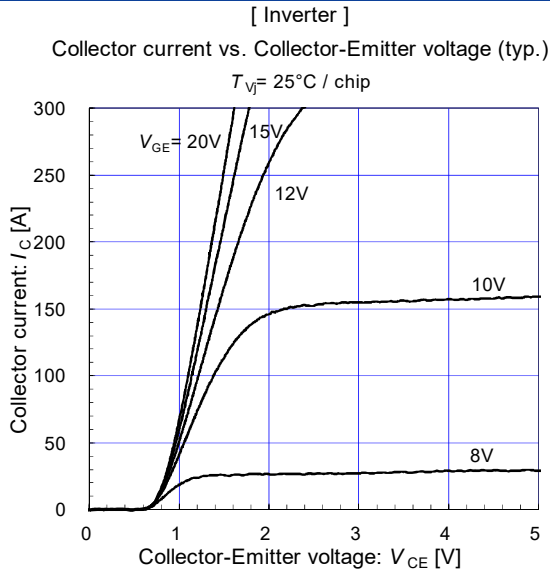
■ Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.33	°C/W
		Inverter FWD	-	-	0.43	
		Brake IGBT	-	-	0.55	
		Brake FWD	-	-	0.86	
		Converter Diode	-	-	0.36	
Contact thermal resistance (1 IGBT+1 FWD) (*1)	$R_{th(c-f)}$	with 1 W/(m·K) thermal grease	-	0.05	-	

(*1) This is the value which is defined mounting on the additional cooling fin with thermal grease.

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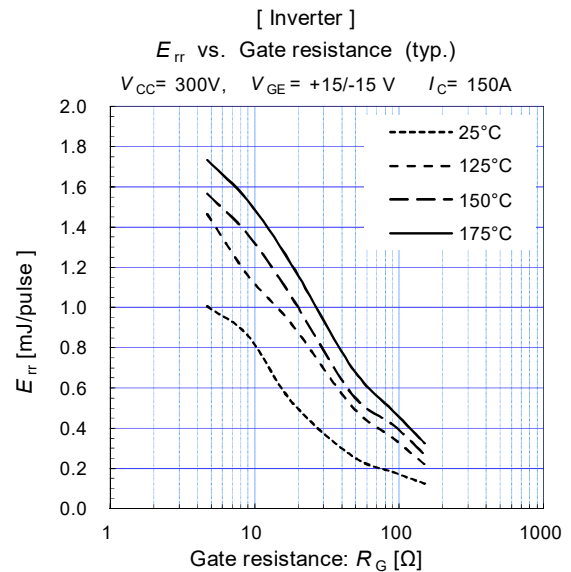
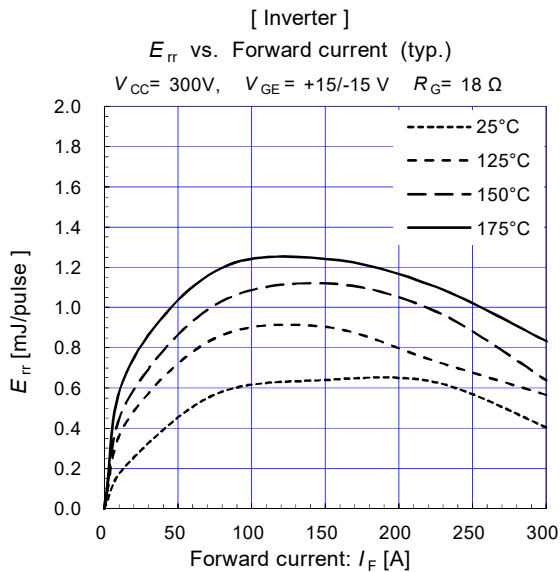
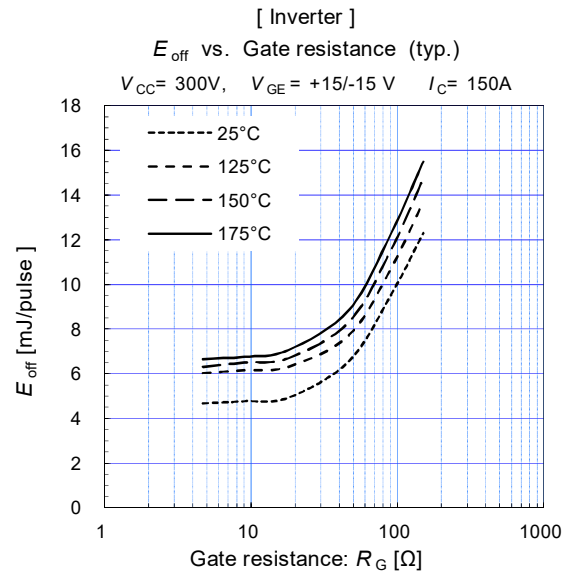
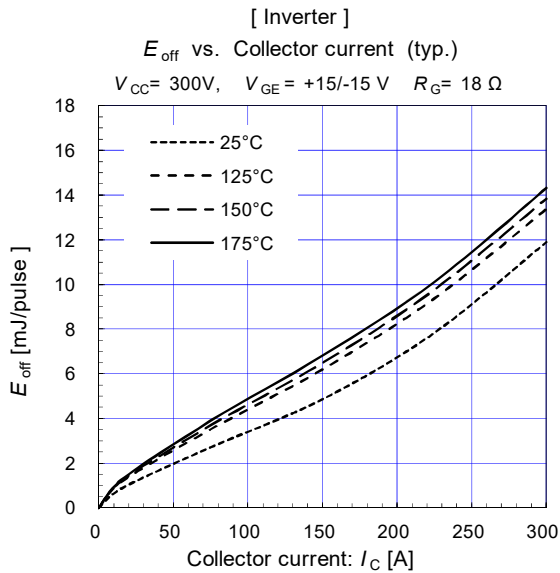
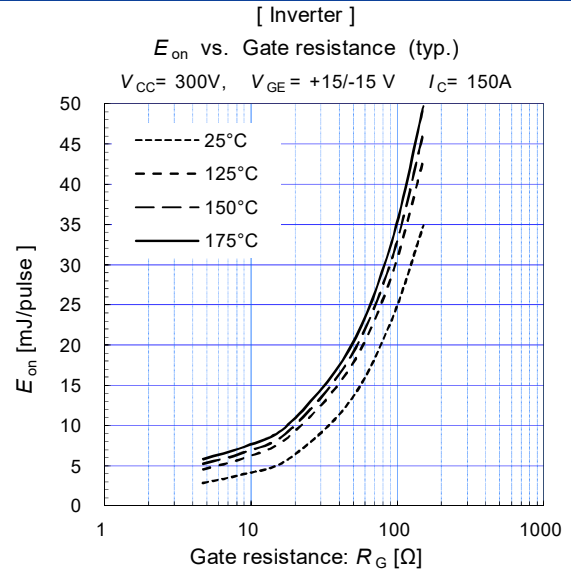
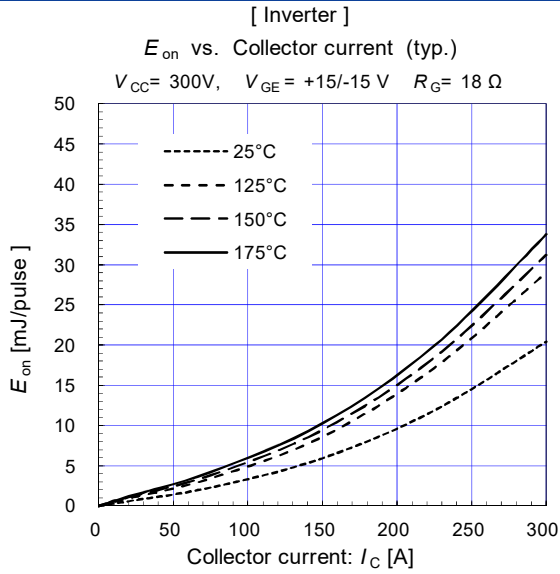


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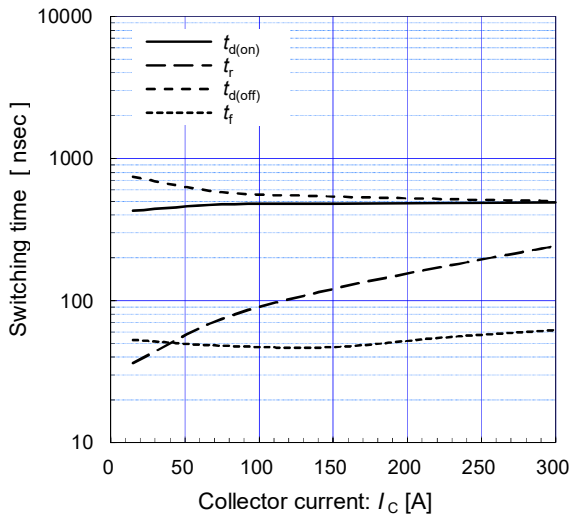
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[Inverter]

Switching time vs. Collector current (typ.)

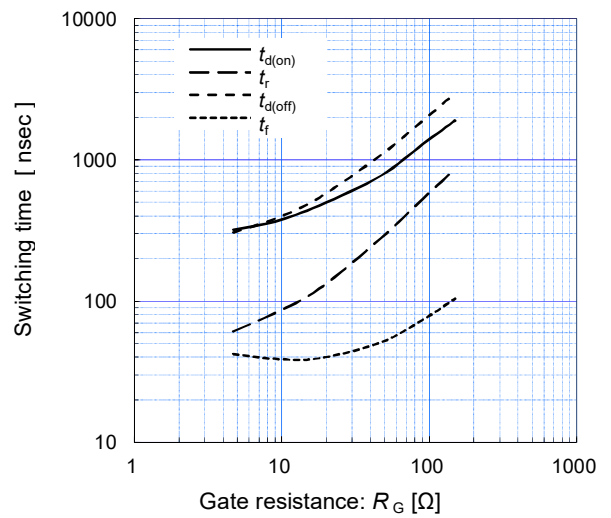
$V_{CC}=300V, R_G=18\Omega, V_{GE}=+15/-15V, T_{Vj}=25^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

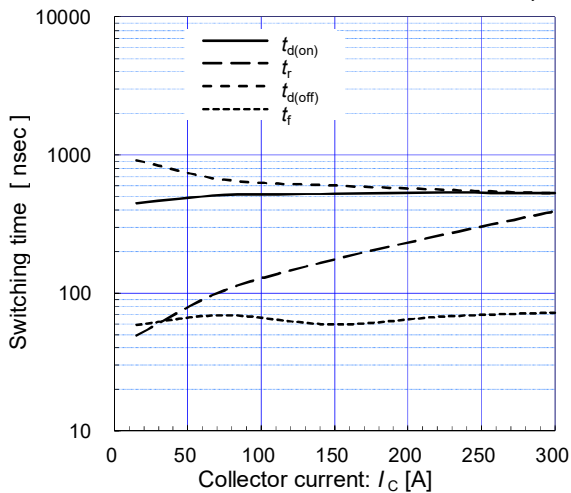
$V_{CC}=300V, I_C=150A, V_{GE}=+15/-15V, T_{Vj}=25^\circ C$



[Inverter]

Switching time vs. Collector current (typ.)

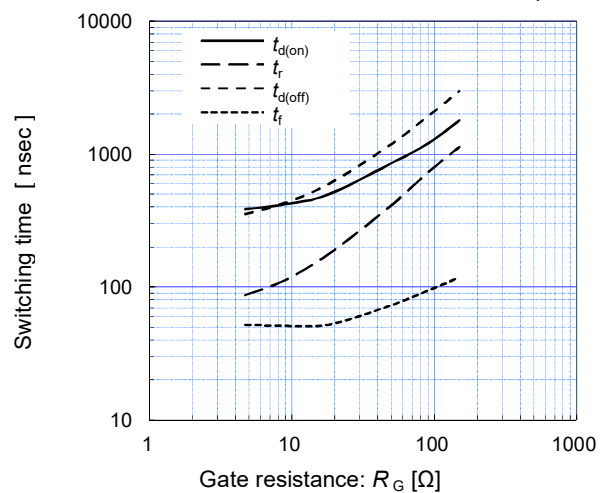
$V_{CC}=300V, R_G=18\Omega, V_{GE}=+15/-15V, T_{Vj}=175^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

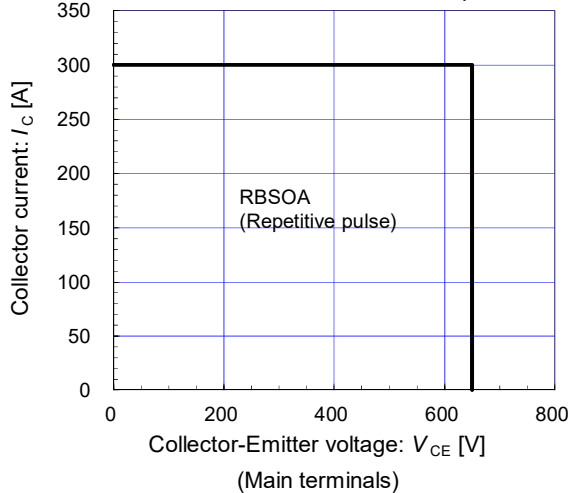
$V_{CC}=300V, I_C=150A, V_{GE}=+15/-15V, T_{Vj}=175^\circ C$



[Inverter]

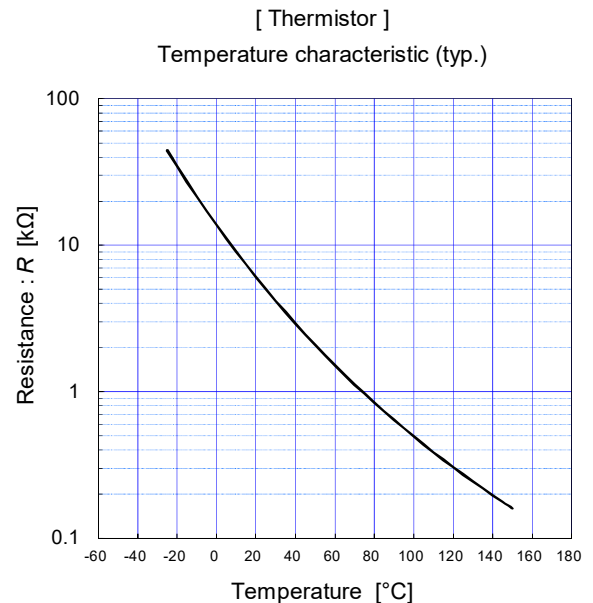
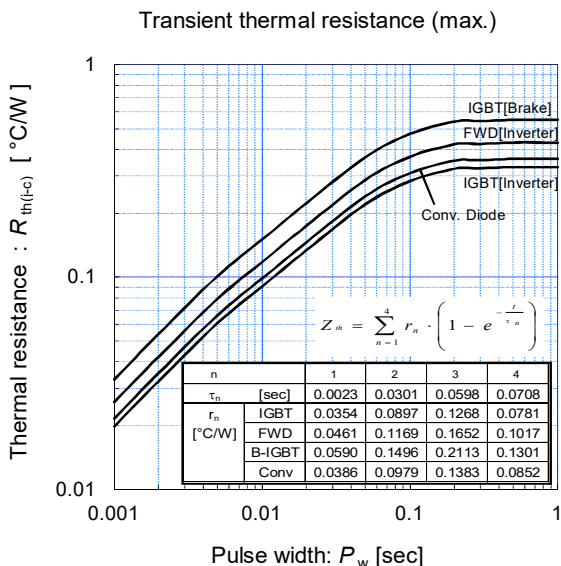
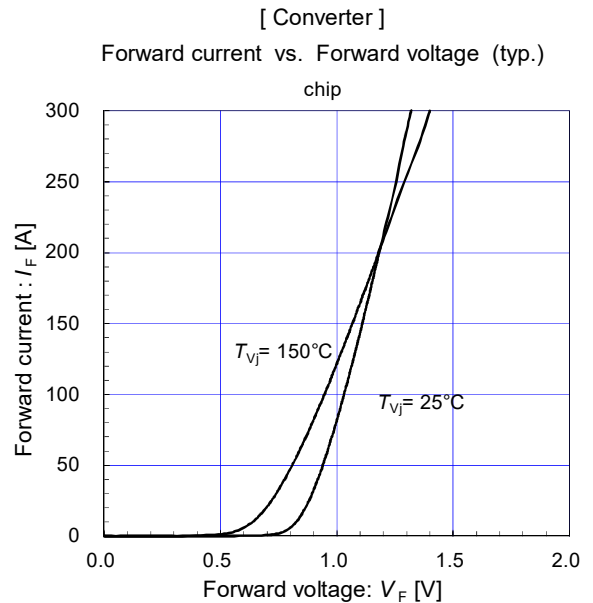
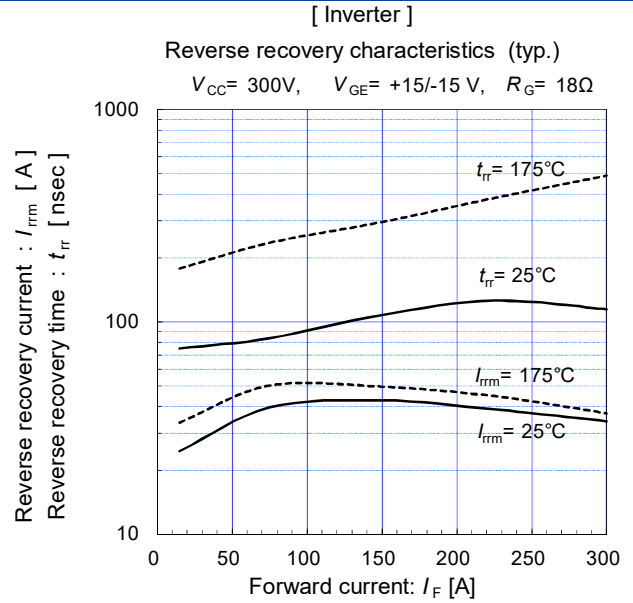
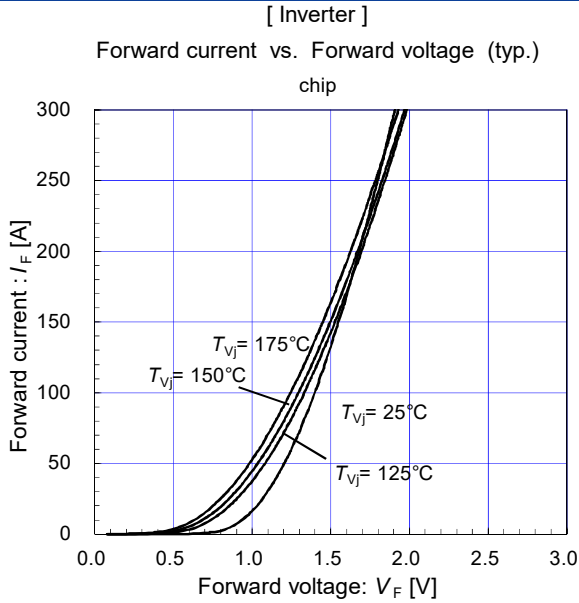
Reverse bias safe operating area (max.)

$V_{GE}=+15/-15V, R_G \ge 18\Omega, T_{Vj}=175^\circ C$



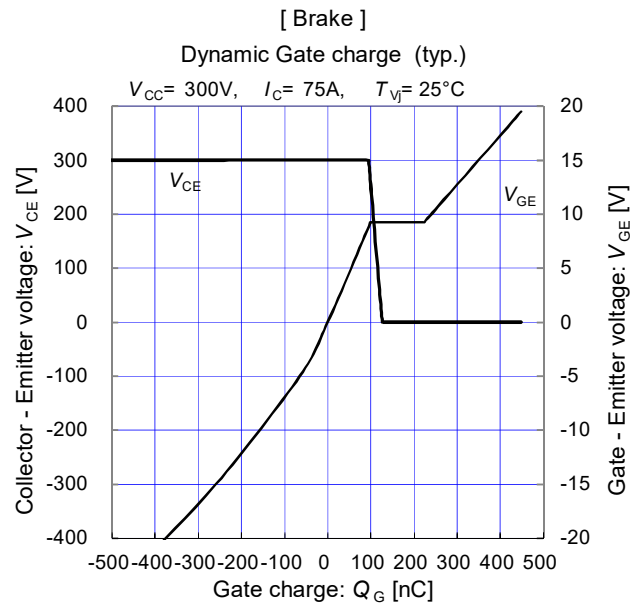
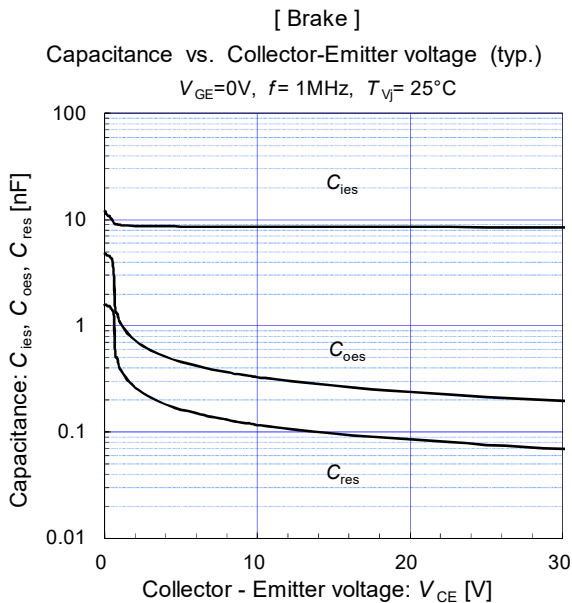
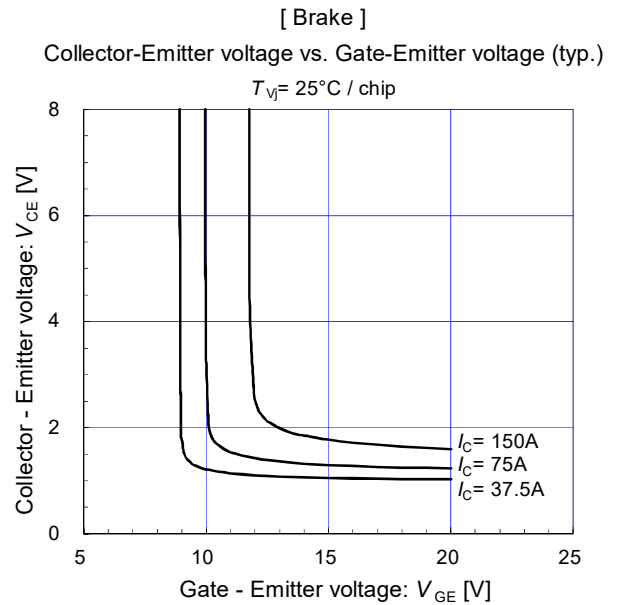
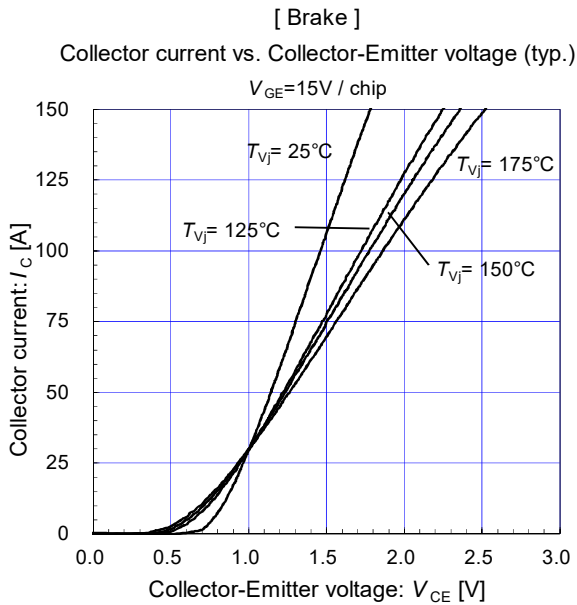
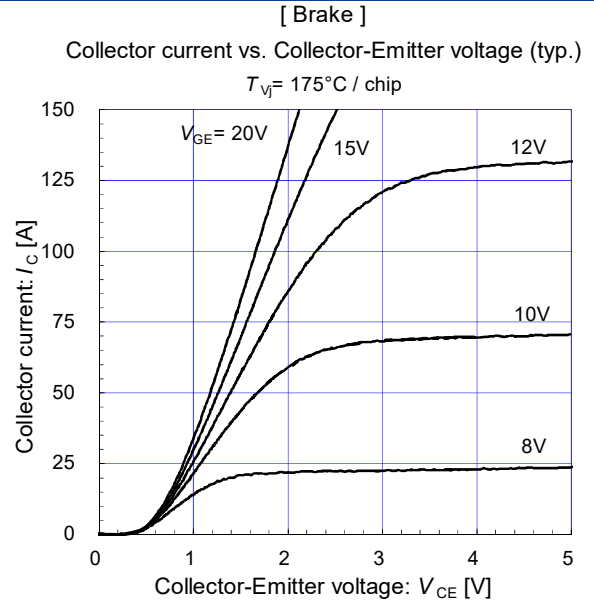
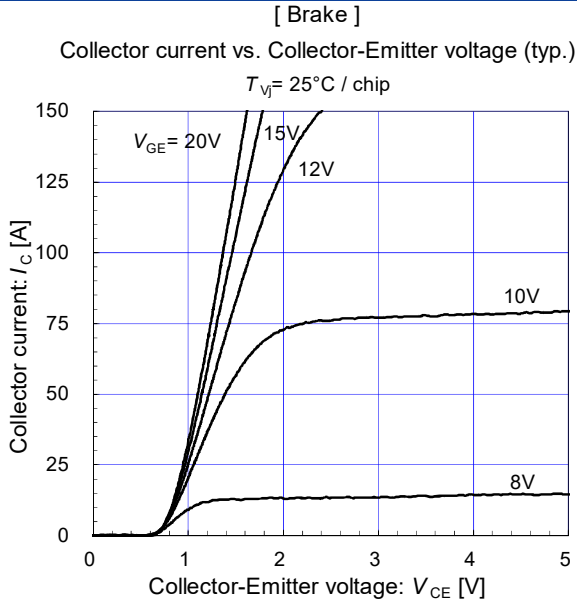
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IGBT Modules

- Please refer to URLs below for further information about products, application manuals and design support.
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